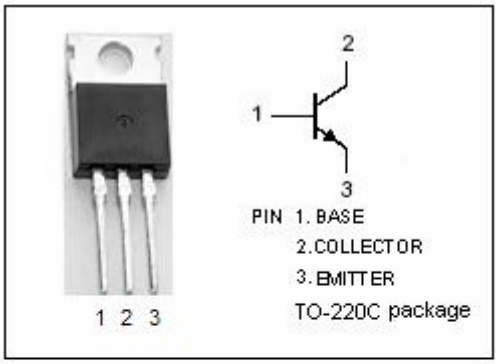
isc Silicon NPN Power Transistor — 2SC1986

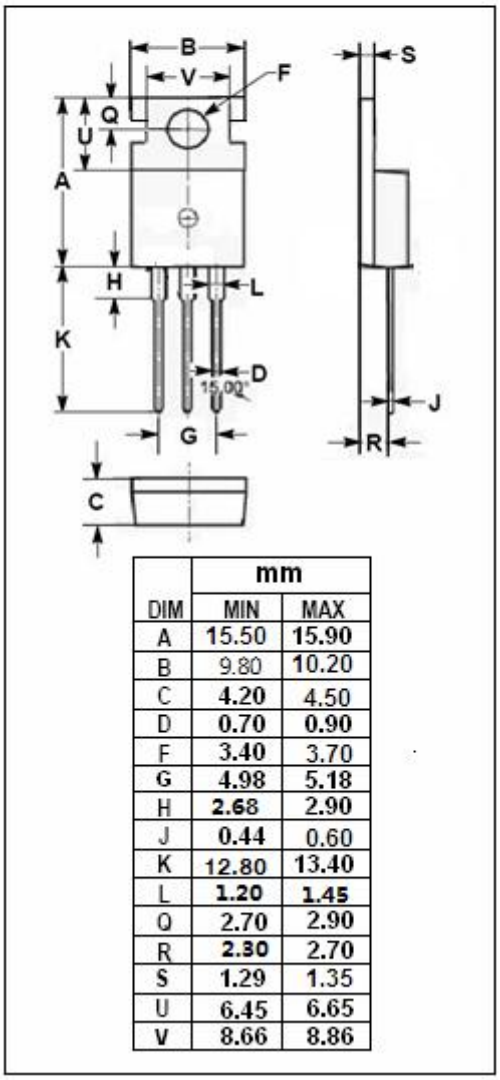


DESCRIPTION

- Silicon NPN tripe diffused mesa
- Collector-Emitter Breakdown Voltage-
  :$V_{(BR)CEO}$= 80(V)(Min.)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- General and industrial purpose



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	6	A
P_C	Total Power Dissipation @ T_C=25℃	40	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 25mA; I_B= 0	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 300mA			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V; I_E= 0			1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C= 0			1	mA
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}= 4V	40			
f_T	Current-Gain—Bandwidth Product	I_E= 500mA; V_{CE}= 12V		10		MHz